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Sommario/riassunto

Capturing the essence of current trends, markets, design tools and technologies in this key field, the internationally acclaimed expert editors have put together a handy reference tailor-made for readers facing the threshold challenges between research and industrial applications.Following a look at general aspects, the book goes on to discuss simulation of industrial growth processes, compound semiconductors, scintillator crystals, oxides, and crystal machining, as well as the potential of crystal growth for sustaining energy and aspects of world crystal production.With many figures,